

# RMM2080

## 2-18 GHz Wideband Variable-Gain Driver Amplifier

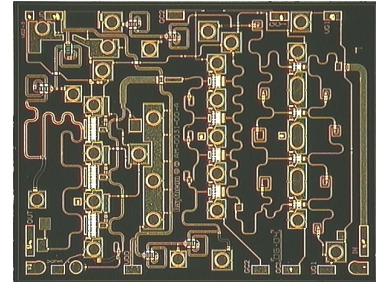
## PRODUCT INFORMATION

## Description

The Raytheon RMM2080 GaAs MMIC device is a three-stage distributed medium-power amplifier with gain control capability. The circuit incorporates ion-implanted, 0.5- $\mu\text{m}$  gate MESFET devices fabricated on a semi-insulating GaAs substrate. The first two stages are 4-cell distributed amplifiers utilizing dual-gate FETs for improved gain per stage and to facilitate gain control (4x125 $\mu\text{m}$  & 4x250 $\mu\text{m}$ ). The third stage is a 3-cell distributed dual-gate FET amplifier designed for high output power and efficiency (3x500 $\mu\text{m}$ ). The RMM2080 amplifier is designed for interconnection with microstrip transmission media using fully automatic assembly techniques.

## Features

- ◆ 2-18 GHz Bandwidth
- ◆ 24 dB Typical Gain
- ◆  $\pm 2$  dB Gain Flatness
- ◆ 20 dBm Output Power Typical
- ◆ Three-Stages of Distributed Amplification
- ◆ Gain Control of up to 70 dB range
- ◆ Dual-Gate Ion-Implanted 0.5- $\mu\text{m}$  FETs
- ◆ Chip Size: 4.14mm x 3.22mm x 0.1mm



## Absolute Maximum Ratings

| Parameter                                   | Symbol               | Value      | Unit |
|---------------------------------------------|----------------------|------------|------|
| Positive Drain DC Voltage (+7V typ)         | Vd                   | +8         | V    |
| Negative DC Voltage                         | Vg                   | -2         | V    |
| Simultaneous (Vg-Vd)                        | Vgd                  | 10         | V    |
| Positive DC Current                         | Id                   | 400        | mA   |
| RF Input Power (from 50W source)            | P <sub>in</sub> (CW) | +8         | dBm  |
| Drain Current                               | I <sub>dd</sub>      | 110        | mA   |
| Operating Baseplate Temperature             | T <sub>case</sub>    | -30 to 85  | °C   |
| Storage Temperature Range                   | T <sub>storage</sub> | -55 to 125 | °C   |
| Thermal Resistance<br>(channel to backside) | R <sub>jc</sub>      | 22         | °C/W |

## Electrical Characteristics

(At 25°C)  
50  $\Omega$  system,  
Vd=+7 V,  
Quiescent current (Idq)  
=300 mA  
GC1, GC2= +1.5 V

| Parameter                | Min | Typ     | Max | Unit  |
|--------------------------|-----|---------|-----|-------|
| Frequency Range          | 2   | -       | 18  | GHz   |
| Gate Supply Voltage (Vg) |     | -0.7    |     | Volts |
| RF Output Power @ -1 dBc |     | 20      |     | dBm   |
| Small Signal Gain        | 18  | 24      |     | dB    |
| Gain Flatness vs. Freq.  | -   | $\pm 2$ |     | dB    |
| Input/Output Return Loss |     | 7       |     | dB    |

| Parameter                                | Min | Typ | Max  | Unit  |
|------------------------------------------|-----|-----|------|-------|
| Gain Control Range                       | 70  |     |      | dB    |
| Gain Control Voltage, GC1&2 <sup>2</sup> | -5  |     | +1.5 | Volts |

## Notes:

1. Typical range of the negative gate voltages is -0.9 to 0.0V to set typical Idq of 300 mA
2. GC1 and GC2 of +1.5V and VG23=open corresponds to maximum gain and power.

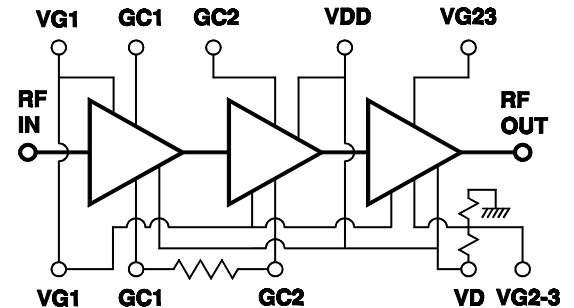
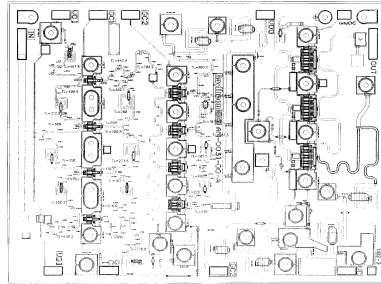
Characteristic performance data and specifications are subject to change without notice.

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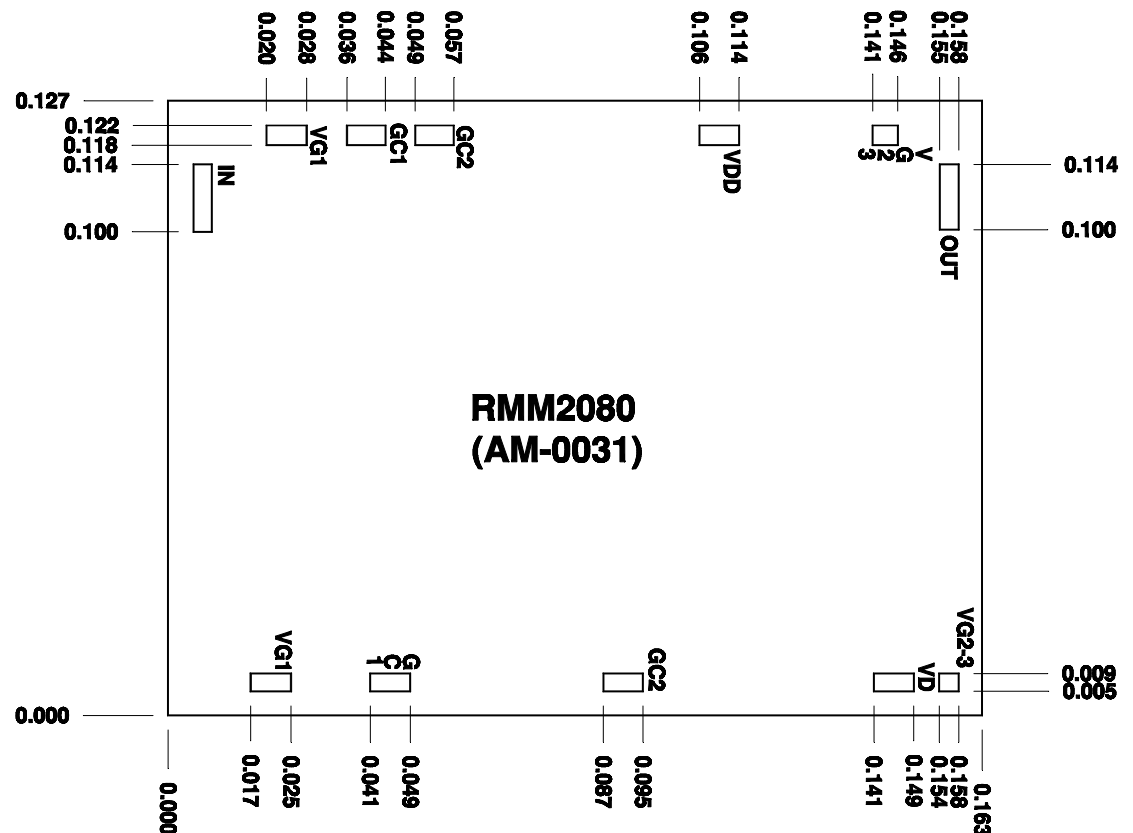
PRODUCT INFORMATION

**Figure 1**  
Block Diagram and  
Circuit Schematic



**Figure 2**  
Location and Size of  
Bonding Pads

*Dimensions in inches*



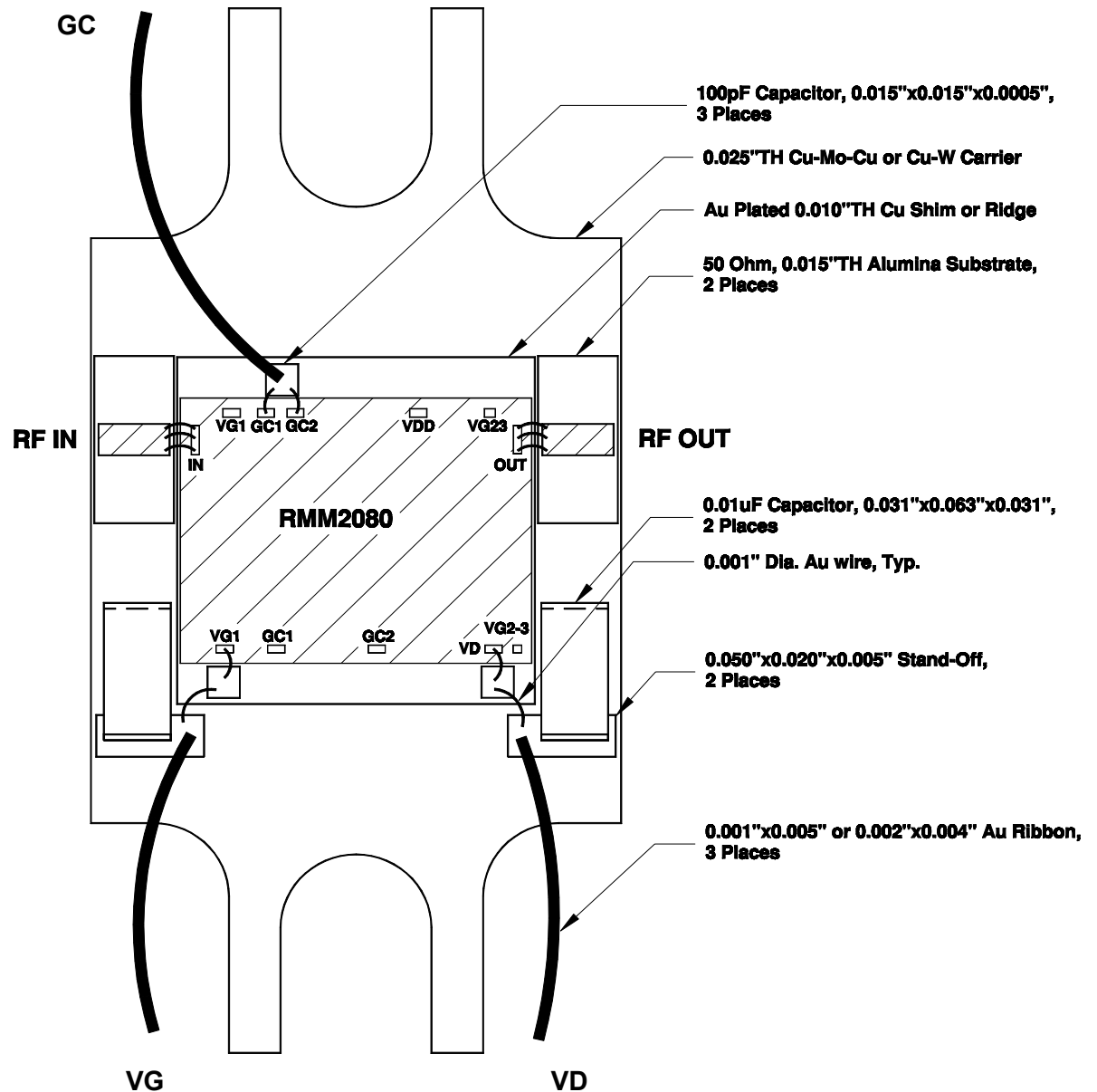
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**Figure 3**  
Example of  
Assembled Module



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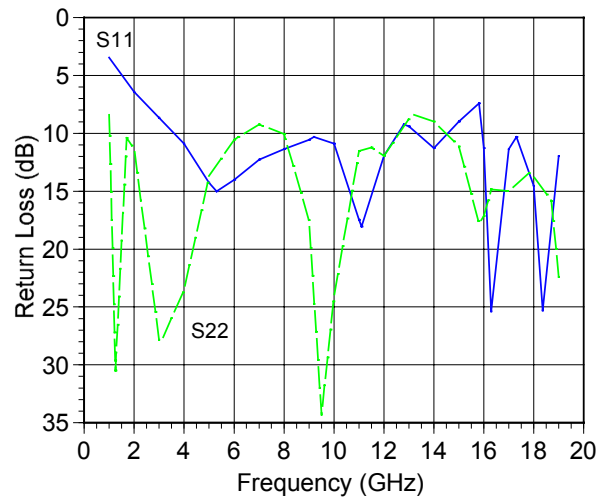
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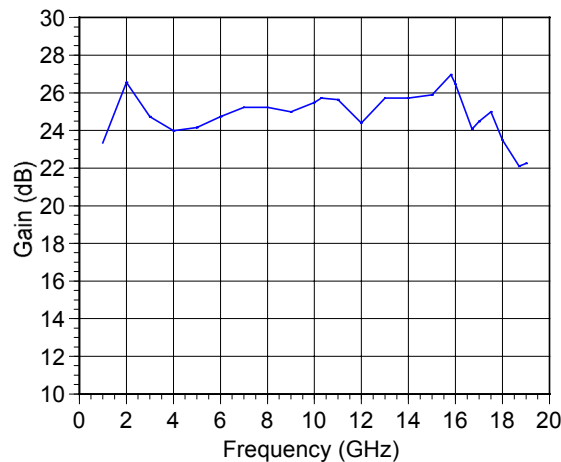
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### Performance Data

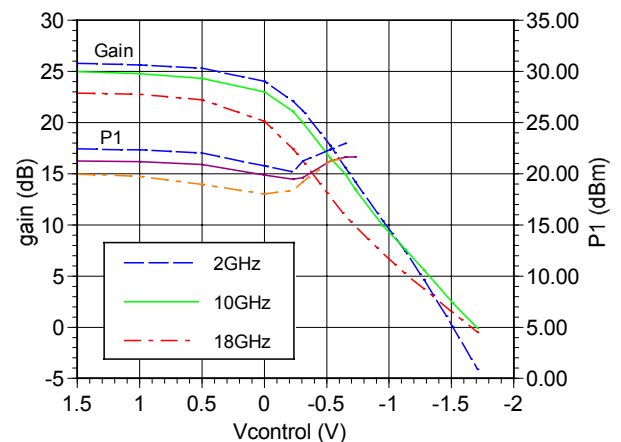
#### Input & Output Return Loss

 $V_d=7.0V$ ,  $I_d=0.3A$ ,  $V_c=1.5V$ 


#### Small Signal Gain

 $V_d=7.0V$ ,  $I_d=0.3A$ ,  $V_c=1.5V$ 


#### Gain & Pout vs. Control Voltage

 $V_d=7.0V$ ,  $I_d=0.3A$  @  $V_c=1.5V$ 


The above data are derived from fixtured measurements which include 3 parallel, 1 mil diameter, 15 mil long, gold bond wires connected to the RF input and output.

The  $I_d$  @ 1 dB compression increases to 0.45 A or thereabouts. The dc supply should be able to support the required current to achieve the above performance.

Characteristic performance data and specifications are subject to change without notice.

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